

Radar Pulsed Power Transistor 55W, 3.1-3.4 GHz, 300µs Pulse, 10% Duty

M/A-COM Products Released, 10 Aug 07

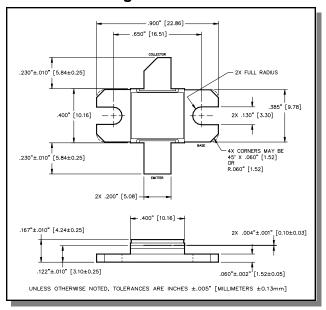
Features

- · NPN silicon microwave power transistors
- · Common base configuration
- Broadband Class C operation
- High efficiency inter-digitized geometry
- Diffused emitter ballasting resistors
- Gold metallization system
- · Internal input and output impedance matching
- Hermetic metal/ceramic package
- · RoHS compliant

Absolute Maximum Ratings at 25°C

Parameter	Symbol	Rating	Units
Collector-Emitter Voltage	V_{CES}	65	V
Emitter-Base Voltage	V_{EBO}	3.0	V
Collector Current (Peak)	Ic	6.5	Α
Power Dissipation @ +25°C	P _{TOT}	350	W
Storage Temperature	T _{STG}	-65 to +200	°C
Junction Temperature	T_J	200	°C

Outline Drawing



Electrical Specifications: T_C = 25 ± 5°C (Room Ambient)

Parameter	Test Conditions	Frequency	Symbol	Min	Max	Units
Collector-Emitter Breakdown Voltage	I _C = 25mA		BV _{CES}	65	-	V
Collector-Emitter Leakage Current	V _{CE} = 36V		I _{CES}	-	5.0	mA
Thermal Resistance	Vcc = 36V, Pout = 55W	F = 3.1, 3.25, 3.4 GHz	R _{TH(JC)}	1	0.5	°C/W
Input Power	Vcc = 36V, Pout = 55W	F = 3.1, 3.25, 3.4 GHz	P _{IN}	-	9.8	W
Power Gain	Vcc = 36V, Pout = 55W	F = 3.1, 3.25, 3.4 GHz	G _P	7.5	-	dB
Collector Efficiency	Vcc = 36V, Pout = 55W	F = 3.1, 3.25, 3.4 GHz	ης	35	-	%
Input Return Loss	Vcc = 36V, Pout = 55W	F = 3.1, 3.25, 3.4 GHz	RL	-	-6	dB
Load Mismatch Tolerance	Vcc = 36V, Pout = 55W	F = 3.25 GHz	VSWR-T	-	2:1	-

PRELIMINARY: Data Sheets contain information regarding a product M/A-COM Technology Solutions has under development. Performance is based on engineering tests. Specifications are typical. Mechanical outline has been fixed. Engineering samples and/or test data may be available. Commitment to produce in volume is not guaranteed.

- North America Tel: 800.366.2266 / Fax: 978.366.2266
- Europe Tel: 44.1908.574.200 / Fax: 44.1908.574.300
- Asia/Pacific Tel: 81.44.844.8296 / Fax: 81.44.844.8298
 Visit www.macomtech.com for additional data sheets and product information.

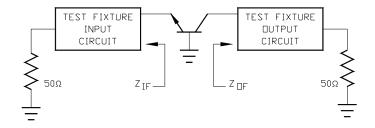


Radar Pulsed Power Transistor 55W, 3.1-3.4 GHz, 300µs Pulse, 10% Duty

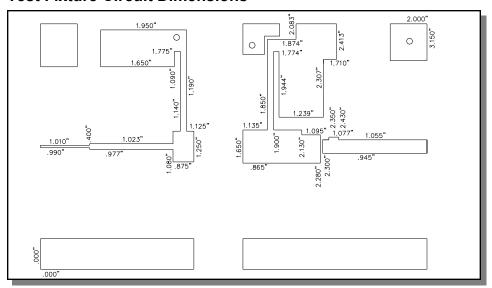
M/A-COM Products Released, 10 Aug 07

RF Test Fixture Impedance

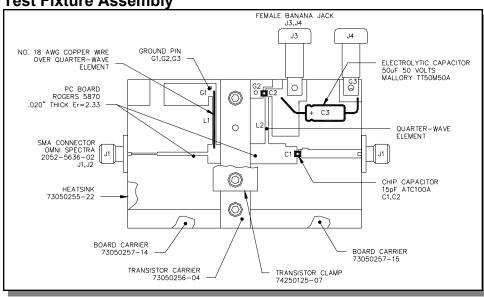
F (GHz)	Z _{IF} (Ω)	Z _{OF} (Ω)
3.10	11.2 - j11.7	8.1 - j5.3
3.25	11.5 - j9.5	7.1 - j4.3
3.40	12.7 - j7.6	6.4 - j3.3



Test Fixture Circuit Dimensions



Test Fixture Assembly



2

PRELIMINARY: Data Sheets contain information regarding a product M/A-COM Technology Solutions has under development. Performance is based on engineering tests. Specifications are typical. Mechanical outline has been fixed. Engineering samples and/or test data may be available. Commitment to produce in volume is not guaranteed.

- North America Tel: 800.366.2266 / Fax: 978.366.2266
- Europe Tel: 44.1908.574.200 / Fax: 44.1908.574.300
- Asia/Pacific Tel: 81.44.844.8296 / Fax: 81.44.844.8298
 Visit www.macomtech.com for additional data sheets and product information.